

SPN5001

DESCRIPTION

The SPN5001 is the N-Channel logic enhancement mode power field effect transistor which is produced with high voltage BiCMOS technology. This device is particularly suited for reducing the no load consumption in PC power, TV power and Adapter.

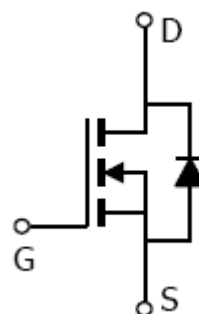
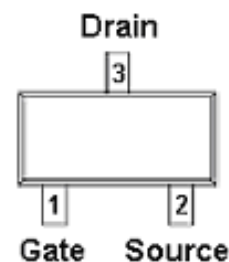
APPLICATIONS

- Desk PC Power Supply
- AC adapter
- LCD TC Power Supply

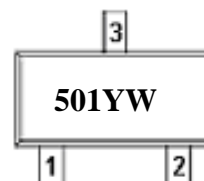
FEATURES

- ◆ 600V/27mA , $R_{DS(ON)} = 300\Omega @ V_{GS} = 10V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-23 package design

PIN CONFIGURATION(SOT-23)



PART MARKING



YW: Date Code

SPN5001

PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN5001S23RGB	SOT-23	501YW

※ SPN5001S23RGB : Tape Reel ; Pb – Free ; Halogen – Free

ABSOLUTE MAXIMUM RATINGS (TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	600	V
Gate –Source Voltage - Continuous	V _{GSS}	±20	V
Continuous Drain Current	I _D	27	mA
Power Dissipation	P _D	0.5	W
Operating Junction Temperature	T _J	-55 ~ 150	°C
Storage Temperature Range	T _{STG}	-55 ~ 150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	250	°C/W

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ELECTRICAL CHARACTERISTICS (T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	600			V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	3.0		4.5		
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =480V, V _{GS} =0V T _J =25°C			25	μA	
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =16mA			300	Ω	
Forward Transconductance	G _{fs(1)}	V _{DS} = 10 V, I _D =16mA		28		mS	
Dynamic							
Total Gate Charge	Q _g	V _{DD} = 200 V, I _D = 0.1 A, V _{GS} = 10 V	1.8	2.5	3.2	nC	
Gate-Source Charge	Q _{gs}				1.3		
Gate-Drain Charge	Q _{gd}				0.8		
Input Capacitance	C _{iss}	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0	8.8	12.5	16.2	pF	
Output Capacitance	C _{oss}			7	10		13
Reverse Transfer Capacitance	C _{rss}			5	7		9
Turn-On Time	t _{d(on)}	V _{DS} = 300 V, I _D = 10m A R _G = 3.3Ω V _{GS} = 10.0 V R _D = 30kΩ		11.5		ns	
	t _r			14.5			
Turn-Off Time	t _{d(off)}				14		
	t _f				120		